

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI SD1490** is a Common Emitter Device Designed for Class A and AB Amplifier Applications in Television Band IV & V Transmitters.

FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting
- Internal Matching

MAXIMUM RATINGS

I_C	8.0 A
V_{CB}	45 V
P_{DISS}	155 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
q_{JC}	1.15 °C/W

PACKAGE STYLE .450 BAL FLG.(A)

	MINIMUM Inches/mm	MAXIMUM Inches/mm		MINIMUM Inches/mm	MAXIMUM Inches/mm
	.055/.140		K	.002/.005	.006/.015
B	.120/.305	.130/.330	L	.055/.140	.065/.165
C	.785/19.94		M	.080/.203	.095/.241
D	.455/11.56	.465/11.81	N		
E	.130/.330		P	.455/11.56	.468/11.89
F	.230/5.84				
G	.128/3.25				
H	.838/21.28	.850/21.59			
I	1.095/27.81	1.105/28.07			
J	.525/13.34	.535/13.59			

1 = Collector 2 = Base
3 = Emitter

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS (PER SIDE)	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 200 mA	30			V
BV_{CBO}	I _C = 50 mA	45			V
BV_{EBO}	I _E = 10 mA	3.0			V
h_{FE}	V _{CE} = 5.0 V I _C = 3.0 A	10		100	---
C_{OB}	V _{CB} = 28 V f = 1.0 MHz		72		pF
G_P	V _{CE} = 26.5 V I _C = 2 X 1.6 A f = 860 MHz	8.0	9.0		dB
G_p	V _{CE} = 28 V I _C = 2 X 250 mA f = 860 MHz P _{out} = 50 W	7.0	8.0		dB
IMD₃	V _{CE} = 26.5 V P _{out} = 25 W f = 860 MHz VISION = -8.0dB SOUND = -10 dB CHROMA = -16dB			-45	dBc